

2N90

Power MOSFET

2A, 900V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **2N90** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **2N90** is universally applied in high efficiency switch mode power supply.

■ FEATURES

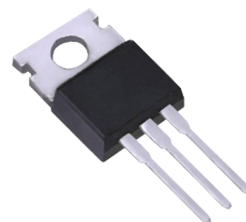
* $R_{DS(ON)} < 7.2\Omega @ V_{GS}=10V, I_D=1.1A$

* High switching speed

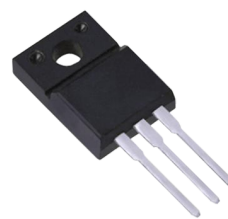
* Improved dv/dt capability

* 100% avalanche tested

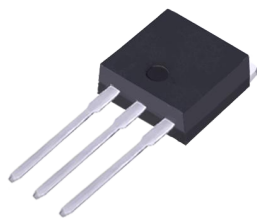
■ SYMBOL



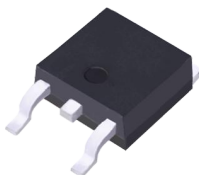
TO-220



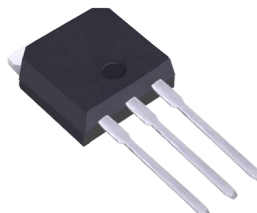
TO-220F



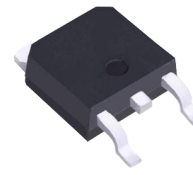
TO-262



TO-263



TO-251



TO-252

2N90

Power MOSFET

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	2.2	A
	Pulsed (Note 2)	I_{DM}	8.8	A
Avalanche Current (Note 2)		I_{AR}	2.2	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	170	mJ
	Repetitive (Note 2)	E_{AR}	8.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation	TO-220	P_D	85	W
	TO-220F		25	
	TO-251/ TO-252		43	
	TO-252D			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 65\text{mH}$, $I_{AS} = 2.2\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 2.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/ TO-252		110	
	TO-252D			
Junction to Case	TO-220	θ_{JC}	1.47	$^\circ\text{C}/\text{W}$
	TO-220F		5	
	TO-251/ TO-252		2.85	
	TO-252D			

■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	900			V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=250\mu\text{A}$		1.0		$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current		I_{DSS}	$V_{DS}=900\text{V}$, $V_{GS}=0\text{V}$			10	μA
			$V_{DS}=720\text{V}$, $T_C=125^\circ\text{C}$			100	
Gate- Source Leakage Current	Forward	I_{GSS}	$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$			+100	nA
	Reverse		$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=1.1\text{A}$		5.6	7.2	Ω
Forward Transconductance		g_{FS}	$V_{DS}=50\text{V}$, $I_D=1.1\text{A}$ (Note 1)		2.0		S
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		480	520	pF
Output Capacitance		C_{OSS}			45		
Reverse Transfer Capacitance		C_{RSS}			7		
SWITCHING PARAMETERS							
Turn-ON Delay Time		$t_{D(ON)}$	$V_{GS}=10\text{V}$, $V_{DD}=30\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1,2)		50		ns
Rise Time		t_R			65		
Turn-OFF Delay Time		$t_{D(OFF)}$			90		
Fall-Time		t_F			45		
Total Gate Charge		Q_G	$V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $I_D=1.3\text{A}$ $I_G=100\mu\text{A}$ (Note 1,2)		16	26	nC
Gate to Source Charge		Q_{GS}			5.5		
Gate to Drain Charge		Q_{GD}			4.5		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				2.2	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				8.8	A
Drain-Source Diode Forward Voltage		V_{SD}	$I_S=2.2\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Reverse Recovery Time		t_{rr}	$I_S=2.2\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt=100\text{A}/\mu\text{s}$		400		ns
Reverse Recovery Charge		Q_{RR}	s (Note 1)		1.6		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

TYPICAL CHARACTERISTICS

